

**Product Summary**

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . Two N Channel MOSFET inside for dual DIE implication.

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A , Trench technology

$R_{DS(ON)}$  to minimize conductive loss

G , C , ,

Dual DIE in one package

Power Management in Notebook Computer

BLDC Motor driver

**Absolute Maximum Ratings  $T_C = 25$** 

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_{D@TC=25}$	45	A
	$I_{D@TC=75}$	34	A
	$I_{D@TC=100}$	28	A
Pulsed Drain Current	$I_{DM}$	135	A
Total Power Dissipation	$P_D@TC=25$	85	W
Total Power Dissipation	$P_D@TA=25$	3.4	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy	$E_{AS}$	102	mJ

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.5	° C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	37	° C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	° C

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V







sions DFN5x6

